

High-reliability discrete products and engineering services since 1977

## MJ900-MJ901-PNP MJ1000-MJ1001 - NPN

#### SILICON POWER DARLINGTON TRANSISTORS

#### **FEATURES**

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
- Available as non-RoHS (Sn/Pb plating), standard, and as RoHS by adding "-PBF" suffix.

#### **MAXIMUM RATINGS**

Rating	Symbol	MJ900 MJ1000	MJ901 MJ1001	Unit
Collector emitter voltage	$V_{CEO}$	60	80	V
Collector emitter voltage	$V_{CBO}$	60	80	V
Emitter base voltage	$V_{\text{EBO}}$	5.0		V
Collector current-Continuous	Ic	10		А
Base current	I <sub>B</sub>	0.1		А
Total power dissipation @ T <sub>C</sub> = 25°C	P <sub>D</sub>	90		W
Derate above 25°C	FD	0.515		W/°C
Operating and storage temperature range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +200		°C
Thermal resistance, junction to case	R <sub>eJC</sub>	1.94		°C/W

**ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise specified)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS		I.			l .
Collector emitter breakdown voltage <sup>(1)</sup> (I <sub>C</sub> = 100mA, I <sub>B</sub> = 0)	MJ900, MJ1000 MJ901, MJ1001	V <sub>(BR)CEO</sub>	60 80	-	V
Collector emitter leakage current					
$(V_{CE} = 60V, R_{BE} = 1k\Omega)$	MJ900, MJ1000		-	1.0	
$(V_{CE} = 80V, R_{BE} = 1k\Omega)$	MJ901, MJ1001	I <sub>CER</sub>	-	1.0	mA
$(V_{CE} = 60V, R_{BE} = 1k\Omega, T_{C} = 150^{\circ}C)$	MJ900, MJ1000		-	5.0	
$(V_{CE} = 80V, R_{BE} = 1k\Omega, T_{C} = 150^{\circ}C)$	MJ901, MJ1001		-	5.0	
Emitter cutoff current		IFBO			mA
$(V_{EB} = 5.0V, I_C = 0)$		IEBO	-	2.0	IIIA
Collector emitter leakage cutoff current					
$(V_{CE} = 30V, I_B = 0)$	MJ900, MJ1000	I <sub>CEO</sub>	-	500	μΑ
$(V_{CE} = 40V, I_B = 0)$	MJ901, MJ1001		-	500	
ON CHARACTERISTICS (1)					
DC current gain					
$(I_C = 3A, V_{CE} = 3.0V)$		h <sub>FE</sub>	1000	-	-
$(I_C = 4A, V_{CE} = 3.0V)$			750	-	
Collector emitter saturation voltage					
$(I_C = 30A, I_B = 12mA)$		V <sub>CE(sat)</sub>	-	2.0	V
$(I_C = 8.0A, I_B = 40mA)$			-	4.0	
Base-emitter voltage		.,			
$(I_C = 3.0A, V_{CE} = 3.0V)$		V <sub>BE(on)</sub>	-	2.5	V
Diode forward voltage					V
(I <sub>F</sub> = 20A)		V <sub>f</sub>	-	5.0	

Note 1: Pulse test: pulse width = 5ms, duty cycle ≤ 2%.



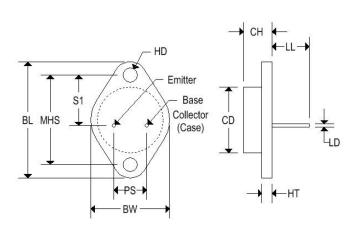
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### **MECHANICAL CHARACTERISTICS**

Case	TO-3
Marking	Alpha-numeric
Polarity	See below



	TO-3					
	Inc	hes	Millimeters			
	Min	Max	Min	Max		
CD	-	0.875	-	22.220		
CH	0.250	0.380	6.860	9.650		
HT	0.060	0.135	1.520	3.430		
BW	-	1.050	-	26.670		
HD	0.131	0.188	3.330	4.780		
LD	0.038	0.043	0.970	1.090		
LL	0.312	0.500	7.920	12.700		
BL	1.550	REF 39.370 F		) REF		
MHS	1.177	1.197	29.900	30.400		
PS	0.420	0.440	10.670	11.180		
<b>S</b> 1	0.655	0.675	16.640	17.150		



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